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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
 CHEN, J. et al.)
 Serial No.:)
 Filing Date:)
 For: METHOD TO IMPROVED)
 LITHOGRAPHIC PATTERNING IN A)
 SEMICONDUCTOR FABRICATION)
 PROCESS)
 _____)
 Continuation Application of:)
 Serial No.: 07/863,791)
 Filed: April 6, 1992)

Bet
1-4-93**Preliminary Amendment**

Box Non-fee Amendments (Pats)
 Commissioner of Patents and Trademarks
 Washington, D.C. 20231

Sirs:

Prior to the examination of the above-identified application, please
 amend the application as follows:

IN THE CLAIMS:

1. (Amended Twice) In a [A] method [of] for lithographically
transferring [printing a two-dimensional feature] a pattern from a mask into a
radiation-sensitive material deposited over a semiconductor substrate [on a
substrate] utilizing an imaging tool, said pattern including a feature having first
and second edges, each of said first and second edges having associated edge
gradients, said first and second edges being spaced in close proximity to one
another such that said associated edge gradients interact causing said feature